

Important notice

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Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET

PDTA123E series PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

Product data sheet Supersedes data of 2004 Apr 07 2004 Aug 02



PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

FEATURES

- Built-in bias resistors
- · Simplified circuit design
- · Reduction of component count
- · Reduced pick and place costs.

APPLICATIONS

- General purpose switching and amplification
- · Inverter and interface circuits
- · Circuit driver.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V _{CEO}	collector-emitter voltage	_	-50	V
Io	output current (DC)	_	-100	mA
R1	bias resistor	2.2	_	kΩ
R2	bias resistor	2.2	_	kΩ

DESCRIPTION

PNP resistor-equipped transistor (see "Simplified outline, symbol and pinning" for package details).

PRODUCT OVERVIEW

TYPE NUMBER	PACKAGE		MARKING CODE	NPN COMPLEMENT	
TYPE NUMBER	PHILIPS	EIAJ	MARKING CODE	INFIN CONIPLEMENT	
PDTA123EE	SOT416	SC-75	5C	PDTC123EE	
PDTA123EEF	SOT490	SC-89	6C	PDTC123EEF	
PDTA123EK	SOT346	SC-59	42	PDTC123EK	
PDTA123EM	SOT883	SC-101	F7	PDTC123EM	
PDTA123ES	SOT54 (TO-92)	SC-43	TA123E	PDTC123ES	
PDTA123ET	SOT23	_	*21 ⁽¹⁾	PDTC123ET	
PDTA123EU	SOT323	SC-70	*42 ⁽¹⁾	PDTC123EU	

Note

^{1. * =} p: Made in Hong Kong.

^{* =} t: Made in Malaysia.

^{* =} W: Made in China.

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL		PINNING		
TYPE NUMBER	SIMPLIFIED OUTLINE AND STMBOL	PIN	DESCRIPTION		
PDTA123ES	1 R1 P2 R2 3	1 2 3	base collector emitter		
PDTA123EE PDTA123EEF PDTA123EK PDTA123ET PDTA123EU	3 1 R1 2 Top view MDB271	1 2 3	base emitter collector		
PDTA123EM	2 R1 R2 R2 Bottom view	1 2 3	base emitter collector		

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

ORDERING INFORMATION

TYPE NUMBER	PACKAGE			
ITPE NUMBER	NAME	DESCRIPTION	VERSION	
PDTA123EE	_	plastic surface mounted package; 3 leads	SOT416	
PDTA123EEF	_	plastic surface mounted package; 3 leads	SOT490	
PDTA123EK	 plastic surface mounted package; 3 leads 		SOT346	
PDTA123EM	-	leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm		
PDTA123ES	_	plastic single-ended leaded (through hole) package; 3 leads SOT		
PDTA123ET	_	plastic surface mounted package; 3 leads	SOT23	
PDTA123EU	_	plastic surface mounted package; 3 leads	SOT323	

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-50	V
V _{CEO}	collector-emitter voltage	open base	_	-50	V
V _{EBO}	emitter-base voltage	open collector	_	-10	V
VI	input voltage				
	positive		_	+10	v
	negative		_	-12	v
Io	output current (DC)		_	-100	mA
I _{CM}	peak collector current		_	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	SOT54	note 1	_	500	mW
	SOT23	note 1	_	250	mW
	SOT346	note 1	_	250	mW
	SOT323	note 1	_	200	mW
	SOT416	note 1	_	150	mW
	SOT490	notes 1 and 2	_	250	mW
	SOT883	notes 2 and 3	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μm copper strip line.

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C		
	SOT54	note 1	250	K/W
	SOT23	note 1	500	K/W
	SOT346	note 1	500	K/W
	SOT323	note 1	625	K/W
	SOT416	note 1	830	K/W
	SOT490	notes 1 and 2	500	K/W
	SOT883	notes 2 and 3	500	K/W

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μm copper strip line.

CHARACTERISTICS

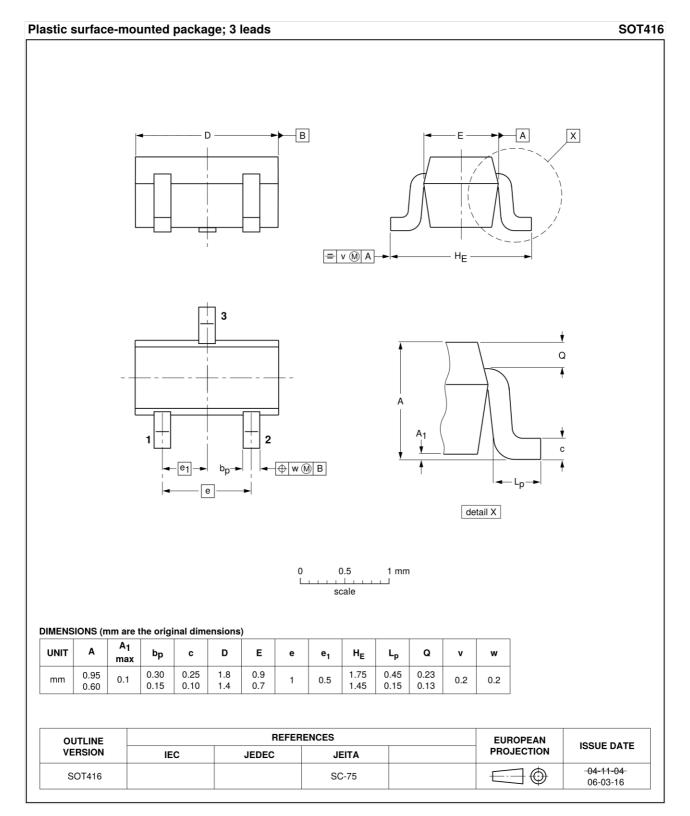
 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	V _{CB} = -50 V; I _E = 0 A	_	_	-100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A}$	_	_	-1	μΑ
		$V_{CE} = -30 \text{ V; } I_{B} = 0 \text{ A; } T_{j} = 150 ^{\circ}\text{C}$	_	_	-50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}$	_	_	-2	mA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -20 \text{ mA}$	30	_	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	_	_	-150	mV
$V_{i(off)}$	input-off voltage	$I_C = -1 \text{ mA}; V_{CE} = -5 \text{ V}$	_	-1.2	-0.5	V
$V_{i(on)}$	input-on voltage	$I_C = -20 \text{ mA}; V_{CE} = -0.3 \text{ V}$	-2	-1.6	_	V
R1	input resistor		1.54	2.2	2.86	kΩ
<u>R2</u> R1	resistor ratio		0.8	1	1.2	
C _c	collector capacitance	$I_E = I_e = 0 \text{ A}; V_{CB} = -10 \text{ V};$ f = 1 MHz	_	_	3	pF

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

PACKAGE OUTLINES



PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

05-07-28

06-03-16

 \bigcirc

Plastic surface-mounted package; 3 leads **SOT490** В А X = v M A 3 **→** | w (M) B detail X 2 mm scale **DIMENSIONS (mm are the original dimensions)** e₁ ${\sf H_E}$ L_{p} UNIT b_p 8.0 0.33 0.2 0.95 mm 1.0 0.5 0.1 0.1 0.6 0.23 REFERENCES OUTLINE VERSION **EUROPEAN ISSUE DATE PROJECTION** IEC **JEDEC JEITA**

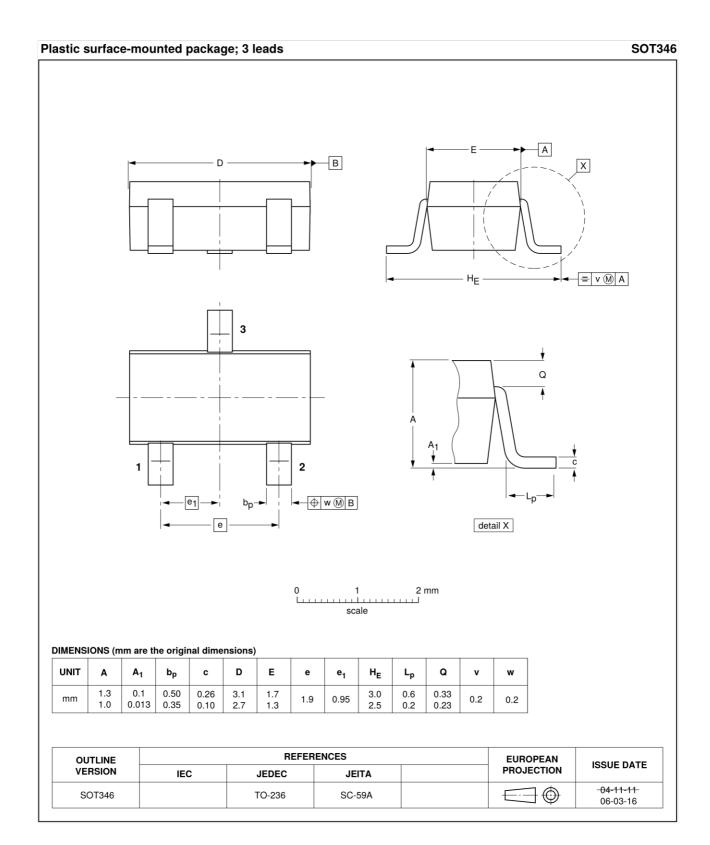
SC-89

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SOT490

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series



PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm **SOT883** e₁ **DIMENSIONS (mm are the original dimensions)** $A^{(1)}$ b_1 e₁ UNIT Ε L_1 е max. 0.50 0.20 0.55 0.62 1.02 0.30 0.30 0.03 mm 0.35 0.65 0.46 0.12 0.47 0.55 0.95 0.22 1. Including plating thickness **REFERENCES** EUROPEAN PROJECTION OUTLINE ISSUE DATE **VERSION** IEC **JEDEC JEITA** 03-02-05 SOT883 SC-101 03-04-03

PNP resistor-equipped transistors; R1 = $2.2 \text{ k}\Omega$, R2 = $2.2 \text{ k}\Omega$

PDTA123E series

Plastic single-ended leaded (through hole) package; 3 leads SOT54 Ε — L₁ —► 2.5 5 mm scale **DIMENSIONS** (mm are the original dimensions) L₁⁽¹⁾ UNIT b₁ D Ε Α b d 5.2 0.48 0.66 0.45 4.8 1.7 4.2 14.5 mm 2.54 1.27 2.5 5.0 0.40 0.55 0.38 4.4 1.4 3.6 12.7 1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

REFERENCES

JEITA

SC-43A

JEDEC

TO-92

EUROPEAN

PROJECTION

ISSUE DATE

04-06-28

04-11-16

2004 Aug 02 10

IEC

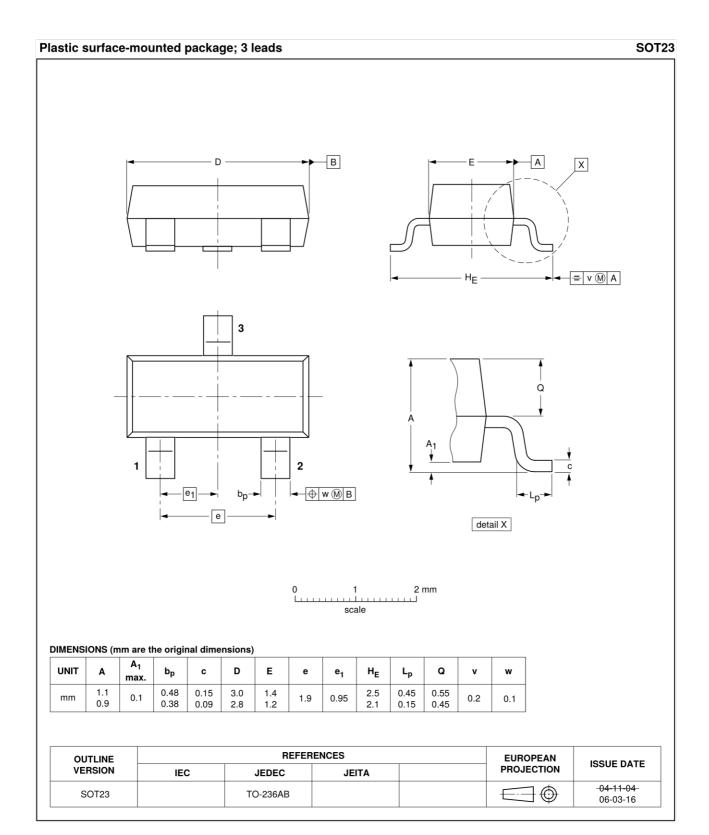
OUTLINE

VERSION

SOT54

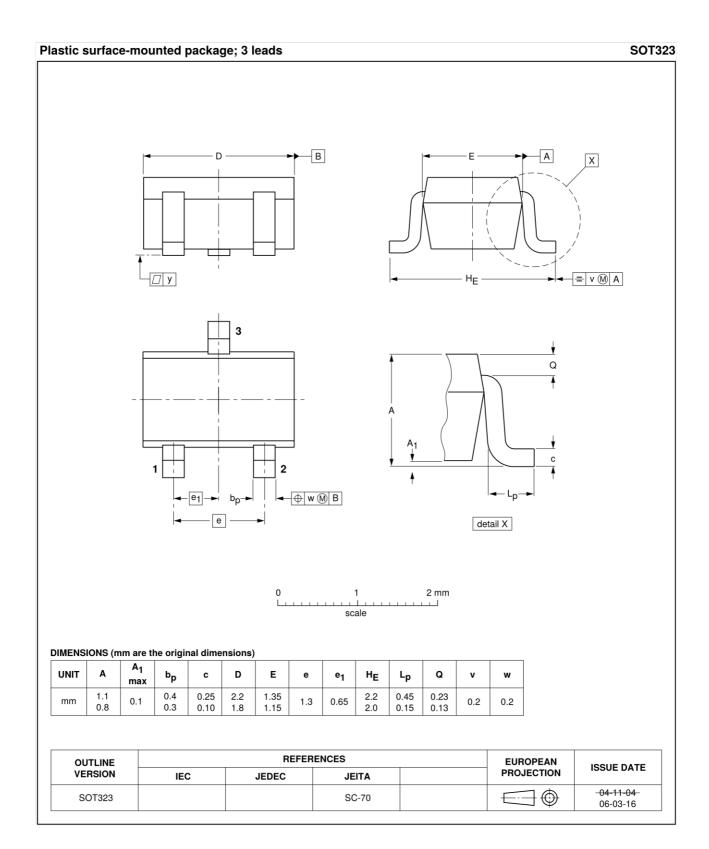
PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series



PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series



PNP resistor-equipped transistors; R1 = $2.2 \text{ k}\Omega$, R2 = $2.2 \text{ k}\Omega$

PDTA123E series

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- The product status of device(s) described in this document may have changed since this document was published
 and may differ in case of multiple devices. The latest product status information is available on the Internet at
 URL http://www.nxp.com.

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2004 Aug 02

NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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